CN-Substituted Ortho-terphenyl Core Based High Triplet Energy Bipolar

Host Materials for Stable and Efficient Blue TADF Device

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1. Experimental Details

1.1 General information

All reagents were purchased from commercial suppliers and used as received. All solvents were used without additional purification. To verify molecular structures of the synthesized materials, ¹H NMR and ¹³C NMR spectrum was measured using Bruker Avance III-400 NMR spectrometer. High-resolution mass spectra were performed using JMS-700 (JEOL, Japan) Gas Chromatography-Mass spectrometer. The transient PL decay was measured using the Quantaurus-Tau fluorescence lifetime measurement system (C11367-03, Hamamatsu Photonics Co.) in a nitrogen-filled atmosphere.

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Figure S1. ¹H NMR of *o*CN-OTP.



Figure S2. ¹³C NMR of *o*CN-OTP.





Figure S3. HRMS of *o*CN-OTP.



Figure S4. ¹H NMR of *m*CN-OTP.



Figure S5. ¹³C NMR of *m*CN-OTP.



Figure S6. HRMS of *m*CN-OTP.



Figure S7. Cyclic Voltammetry (CV) cure of DCz-OTP, oCN-OTP and mCN-OTP.



Figure S8. TGA and DSC graphs of DCz-OTP, *o*CN-OTP and *m*CN-OTP.



Figure S9. Spectral overlap between PL emission of three host and absorption of DBA-DI TADF dopant.



Figure S10. (a) Comparison of phosphorescence spectra of DCz-OTP, *o*CN-OTP, *m*CN-OTP and DBA-DI in toluene and (b) film TRPL of 30% of DBA-DI in DCz-OTP, *o*CN-OTP and *m*CN-OTP. (c) exponential fitting curve for determining decay time.



Figure S11. Device lifetimes of *m*CN-OTP host device depending on the thickness of BPPB at initial luminance of $1,000 \text{ cd/m}^2$.



Figure S12. Calculation of Bond dissociation energies of host materials in neutral, anion, and cation states.